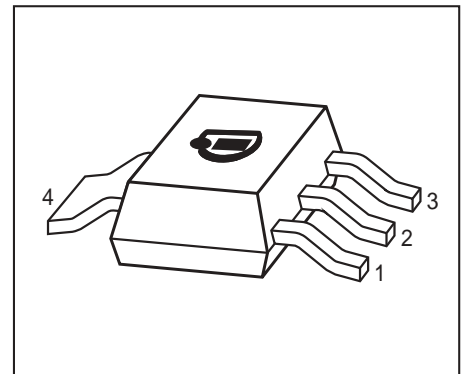


NPN Silicon RF Transistor*

- For low-distortion broadband output amplifier stages in antenna and telecommunication systems up to 2 GHz at collector currents from 120 mA to 250 mA
- Power amplifiers for DECT and PCN systems
- Integrated emitter ballast resistor
- $f_T = 5.5$ GHz

* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFG235	BFG235	1 = E	2 = B	3 = E	4 = C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	15	V
Collector-emitter voltage	V_{CES}	25	
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	300	mA
Base current	I_B	40	
Total power dissipation ¹⁾ $T_S \leq 80^\circ\text{C}$	P_{tot}	2	W
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 35	K/W

¹ T_S is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

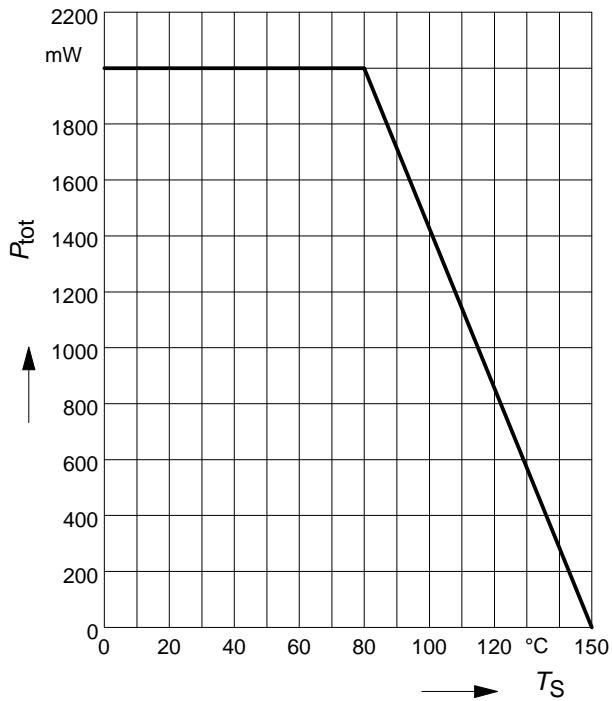
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 25\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	200	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	-	-	2	μA
DC current gain- $I_C = 200\text{ mA}$, $V_{CE} = 8\text{ V}$, pulse measured	h_{FE}	75	120	160	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

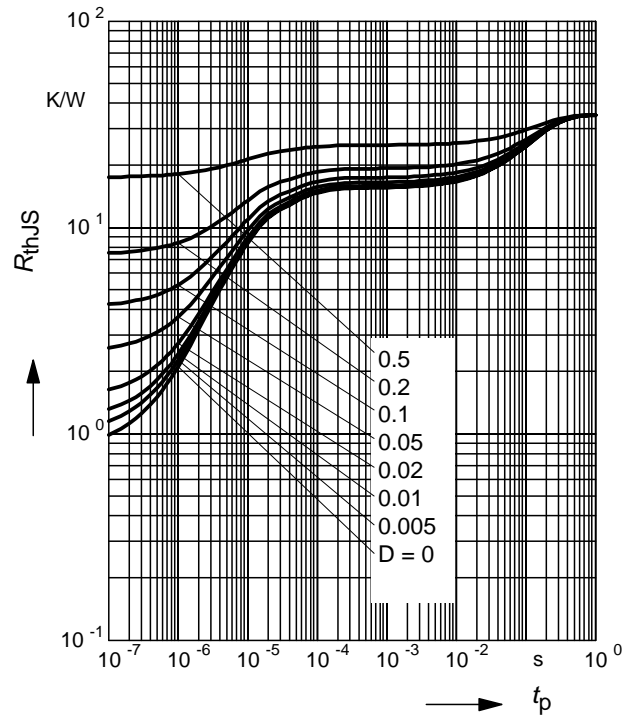
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 200\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 200\text{ MHz}$	f_T	4	5.5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	2.2	3	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	1.5	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	14	-	
Noise figure $I_C = 60\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$	F	-	1.7	-	dB
Power gain, maximum available ¹⁾ $I_C = 200\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$	G_{ma}	-	12.5	-	
Transducer gain $I_C = 200\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 900\text{ MHz}$	$ S_{21e} ^2$	-	6.5	-	dB
Third order intercept point at output $V_{CE} = 8\text{ V}$, $I_C = 200\text{ mA}$, $f = 900\text{ MHz}$, $Z_S = Z_L = 50\Omega$	IP_3	-	33	-	dBm

$$^1G_{ma} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$$

Total power dissipation $P_{\text{tot}} = f(T_S)$

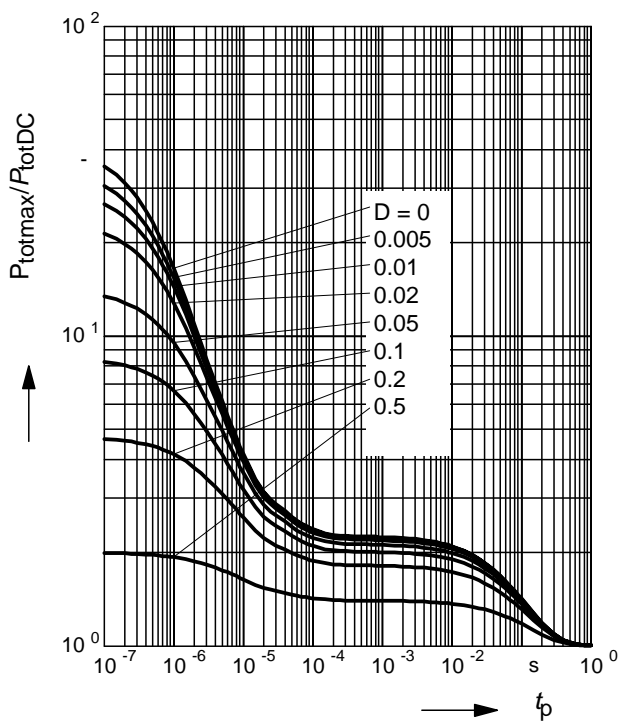


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

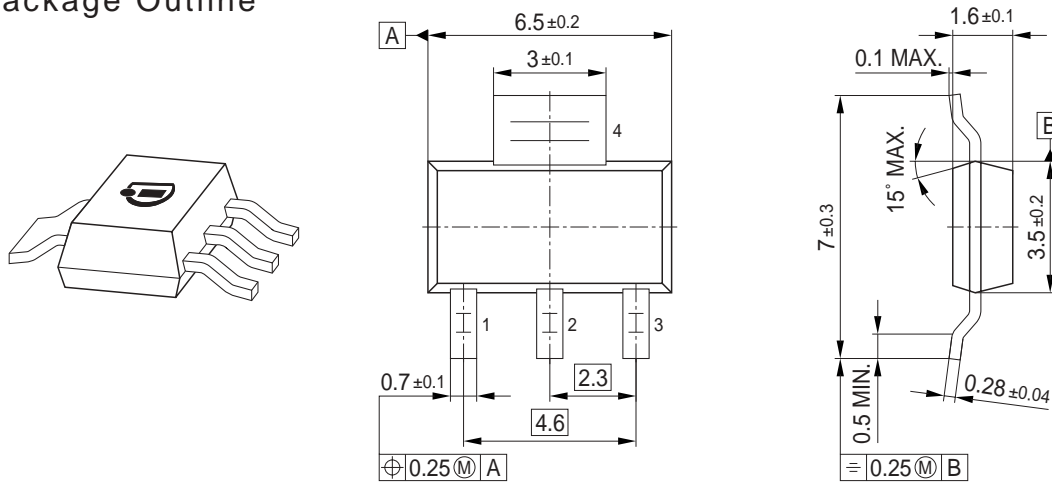


Permissible Pulse Load

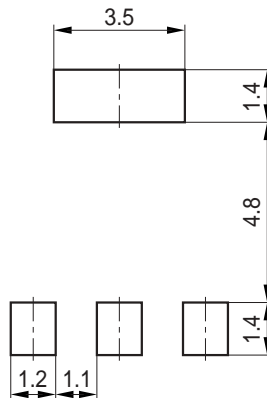
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



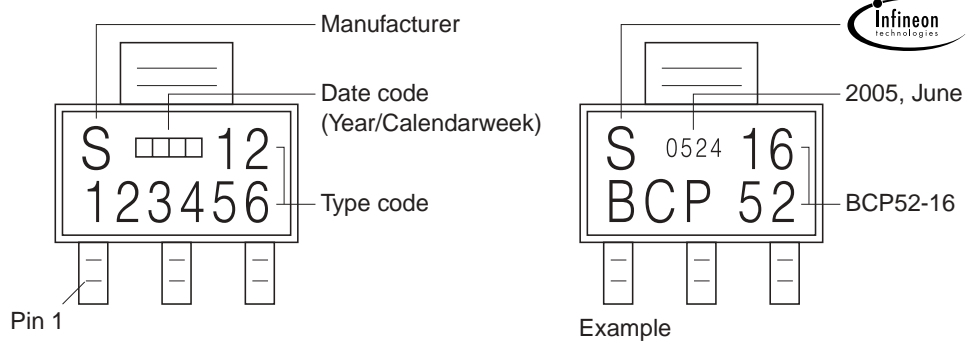
Package Outline



Foot Print

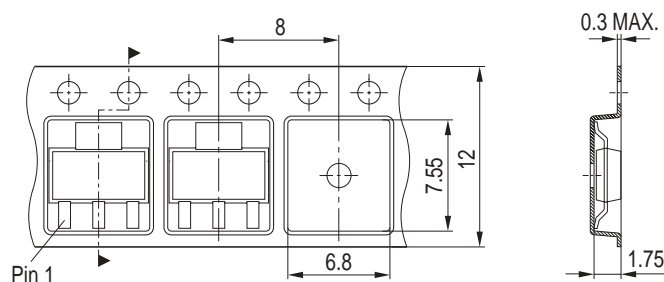


Marking Layout



Packing

Reel $\varnothing 180 \text{ mm}$ = 1.000 Pieces/Reel
 Reel $\varnothing 330 \text{ mm}$ = 4.000 Pieces/Reel



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